



# 3DD7

## NPN Silicon Low Frequency High Power Transistor



### Features:

1. Using triple-diffusion process.Excellent capacity in anti-burnout.Excellent second breakdown capacity.
2. Good temperature stability.Excellent thermal fatigue capability.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for Low-speed switch,low frequency power amplify,power adjustment.
5. Quality Class: JP, JT, JCT, GS, G, G+

### TECHNICAL DATA:

(Ta = 25°C )

Parameter name	Symbols	Unit	Specifications									Test Condition
			A	B	C	D	E	F	G	H	I	
Collector-Emitter Voltage	V <sub>CEO</sub>	V	50	100	150	200	250	300	400	500	600	
Emitter-Base Voltage	V <sub>EBO</sub>	V	5									
Max. Collector Current	I <sub>CM</sub>	A	A~F:7.5, G~I:3.5									
Max. Collector Dissipation	P <sub>CM</sub>	W	75									(Tc:75°C)
Junction Temperature	T <sub>jm</sub>	°C	175									
Storage Temperature	T <sub>stg</sub>	°C	-55~+175									
Collector-Emitter Leakage Current	I <sub>CEO</sub>	mA	Max.:3.0									A:V <sub>CE</sub> =30V;B:V <sub>CE</sub> =50V; C~I:V <sub>CE</sub> =100V
Collector- Emitter Saturation Voltage Drop	V <sub>CE(sat)</sub>	V	Max.:1.2									A~F: I <sub>C</sub> =3.75A, I <sub>B</sub> =0.38A
			Max.:2.0									G~I: I <sub>C</sub> =2.0A, I <sub>B</sub> =0.4A
DC Current Gain	h <sub>FE</sub>		Max.:120						Min.:15			A~F: V <sub>CE</sub> =5V, I <sub>C</sub> =3.75A
			Max.:120						Min.: 7			G~I:V <sub>CE</sub> =10V, I <sub>C</sub> =2.0A
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	V	A	B	C	D	E	F	G	H	I	I <sub>C</sub> =3mA
			50	100	150	200	250	300	400	500	600	
E-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	V	5									I <sub>E</sub> =2mA

### h<sub>FE</sub> Colored:

Color	Brown	Red	Orange	Yellow	Green	Blue
h <sub>FE</sub>	7~15	15~25	25~40	40~55	55~80	80~120

### Outline and Dimensions: